

AMENDMENTS TO THE CLAIMS

1. - 30. (Canceled)

31. (Currently Amended) A substrate processing apparatus, comprising:

resist solution supplying means for supplying a resist;

affinitive material supplying means for supplying an affinitive material, the

affinitive material being affinitive with a developing solution;

mixing means for mixing the resist supplied from the resist solution supplying means and the affinitive material supplied from the affinitive material supplying means, to obtain a mixed resist;

resist film forming means for coating a the mixed resist on a substrate so as to form a mixed resist film thereon; and

controlling means for controlling a distribution of a dissolving characteristic of the mixed resist against a the developing solution used for developing the mixed resist in a direction of a thickness of the mixed resist film ~~such that the resist includes an uneasily-dissolvable layer on a front side and an easily-dissolvable layer on a rear side~~, prior to developing the substrate to which the mixed resist is coated.

32. (Currently Amended) The substrate processing apparatus as set forth in claim 31,

~~wherein the resist film forming means coats on the substrate a resist that contains a material having an affinity against the developing solution used for the developing process, and~~

wherein the controlling means performs a predetermined process for the mixed resist coated on the substrate so as to nonuniformly distribute the material in the direction of the thickness of the mixed resist film.

33. (Previously Presented) The substrate processing apparatus as set forth in claim 32,

wherein the predetermined process has at least one of a heating process and a pressure reducing process.

34. (Currently Amended) The substrate processing apparatus as set forth in claim 31, wherein the controlling means supplies the developing solution used for the developing process to the mixed resist coated on the substrate.

35. (Withdrawn) A substrate processing method which uses the apparatus according to claim 31, comprising:

- (a) coating a resist on a substrate so as to form a resist film thereon;
- (b) controlling a distribution of a dissolving characteristic of the resist against a developing solution used for developing the resist in a direction of a thickness of the resist film such that the resist includes an uneasily-dissolvable layer on a front side and an easily-dissolvable layer on a rear side, prior to developing the substrate to which the resist is coated.

36. (Withdrawn) The substrate processing method as set forth in claim 35, wherein the step (a) has the step of coating on the substrate a resist that contains a material having an affinity against the developing solution used for the developing process *r* and

wherein the step (b) has the step of performing a predetermined process for the resist coated on the substrate so as to nonuniformly distribute the material in the direction of the thickness of the resist film.

37. (Withdrawn) The substrate processing method as set forth in claim 36, wherein the predetermined process has at least one of a heating process and a pressure reducing process.

38. (Withdrawn) The substrate processing method as set forth in claim 35,

wherein the step (b) has the step of supplying the developing solution used for the developing process to the resist coated on the substrate.